TOSHIBA Diode Silicon Epitaxial Planar Type

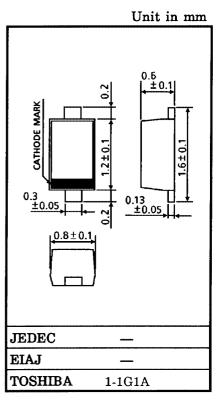
JDV2S02E

VCO for UHF band

- Small Package
- High Capacitance Ratio: $C_{1V}/C_{4V} = 2.0$ (typ.)
- Low Series Resistance $: r_s = 0.60 \Omega$ (typ.)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Reverse voltage	V _R	10	V
Junction temperature	Тј	125	°C
Storage temperature range	T _{stg}	-55~125	°C



Weight: 0.0014 g

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Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse voltage	V _R	$I_R = 1 \ \mu A$	10	_	_	V
Reverse current	I _R	V _R = 10 V	_	_	3	nA
Capacitance	C _{1V}	V _R = 1 V, f = 1 MHz	1.8	2.05	2.3	pF
	C _{4V}	$V_R = 4 V$, f = 1 MHz	0.83	1.03	1.23	
Capacitance ratio	C _{1V} /C _{4V}	_	1.8	2	_	_
Series resistance	r _s	V _R = 1 V, f = 470 MHz	_	0.6	0.8	Ω

Note: Signal level when capacitance is measured. V_{sig} = 100 mV_{rms}

Marking



TOSHIBA

